

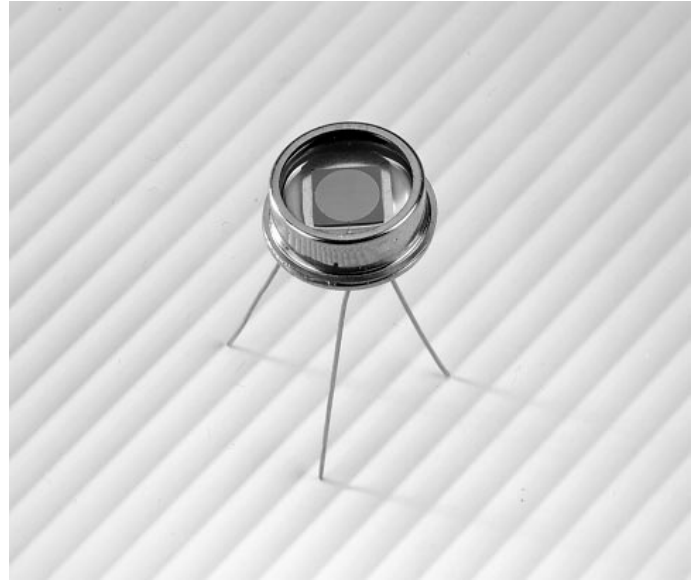
Large Area InGaAs P-I-N Photodiode 5 mm Active Diameter

Features

- High responsivity at 1300, 1550 and 850 nm
- High shunt resistance for low noise
- Low dark current for high accuracy
- Packaged in a TO-8 can

Applications

- Fiber optic test instruments
 - Optical power meters
 - Optical attenuation test sets
- Near infrared spectroscopy
- Near infrared sensing



Preliminary Specifications Optical/Electrical Characteristics

(@25°C, $V_R = 0V$ Unless otherwise noted)

ETX5000T8

Parameter	Min.	Typ.	Max.	Units
Responsivity at 850 nm	0.10	0.20		A/W
Responsivity at 1300 nm	0.80	0.90		A/W
Responsivity at 1550 nm		0.95		A/W
Capacitance ¹		1.1	2.0	nF
Shunt Resistance	200	800		k Ohms
Dark current ¹		3	10	uA

Notes:

¹ $V_R = 1V$

Maximum Ratings

Parameter	Rating	Units
Reverse voltage	2	V
Reverse current ^A	10	mA
Forward Current ^B	10	mA
Power Dissipation	50	mW
Operating Temperature	-40 / +85	°C
Storage Temperature	-40 / +85	°C

Notes:

^A Under reverse bias, current at which device may be damaged.

^B Under forward bias, current at which device may be damaged.

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